

H5N2522FP-E0-E

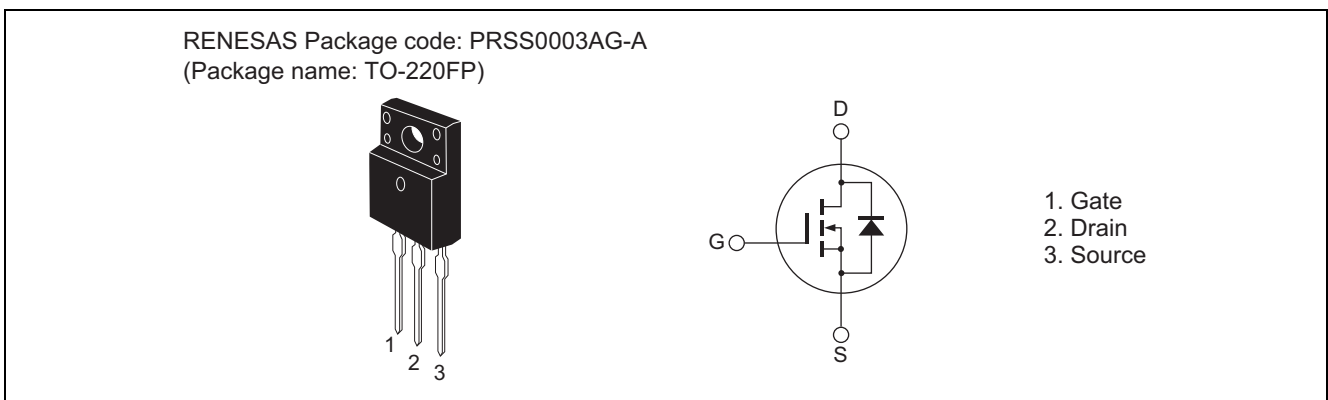
250V - 12A - MOS FET
High Speed Power Switching

R07DS0862EJ0100
Rev.1.00
Jul 27, 2012

Features

- Low on-resistance
 $R_{DS(on)} = 0.13 \Omega$ typ. (at $I_D = 6 A$, $V_{GS} = 10 V$, $T_a = 25^\circ C$)
- Low leakage current
- High speed switching
- Built-in fast recovery diode

Outline



Absolute Maximum Ratings

($T_a = 25^\circ C$)

Item	Symbol	Ratings	Unit
Drain to Source voltage	V_{DSS}	250	V
Gate to source voltage	V_{GSS}	± 30	V
Drain current	I_D	12	A
Drain peak current	$I_{D(pulse)}$ ^{Note1}	48	A
Body-Drain diode reverse Drain current	I_{DR}	12	A
Body-Drain diode reverse Drain peak current	$I_{DR(pulse)}$ ^{Note1}	48	A
Avalanche current	I_{AP} ^{Note3}	12	A
Avalanche energy	E_{AR} ^{Note3}	9	mJ
Channel dissipation	P_{ch} ^{Note2}	35	W
Channel to case thermal impedance	θ_{ch-c}	3.57	$^\circ C/W$
Channel temperature	T_{ch}	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

Notes: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$
 2. Value at $T_c = 25^\circ C$
 3. $ST_{ch} = 25^\circ C$, $T_{ch} \leq 150^\circ C$

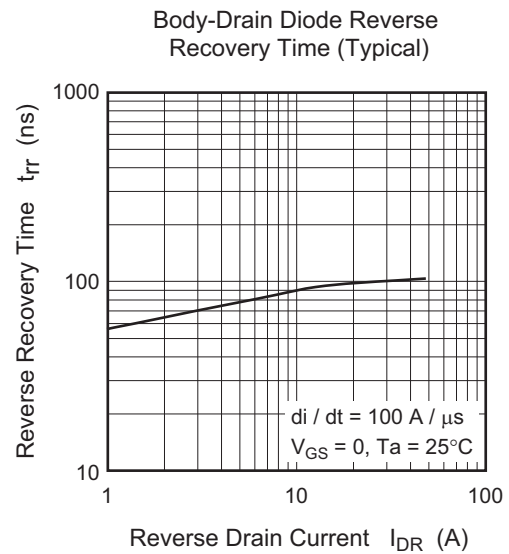
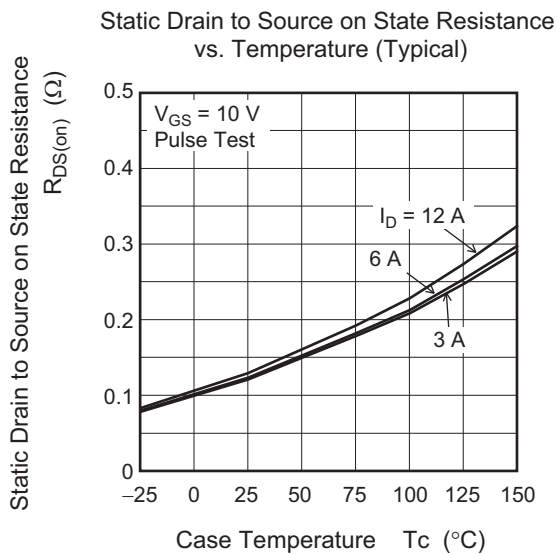
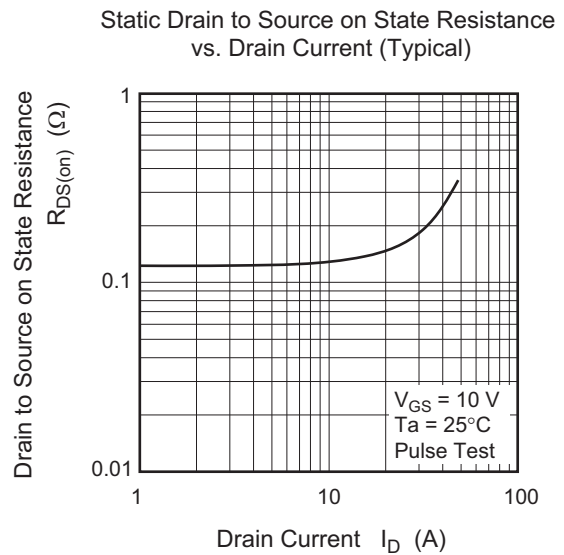
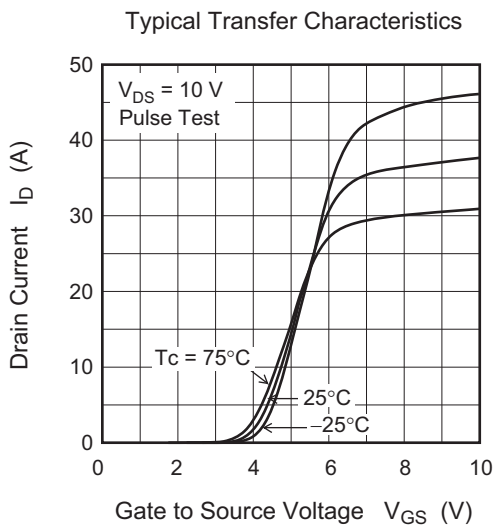
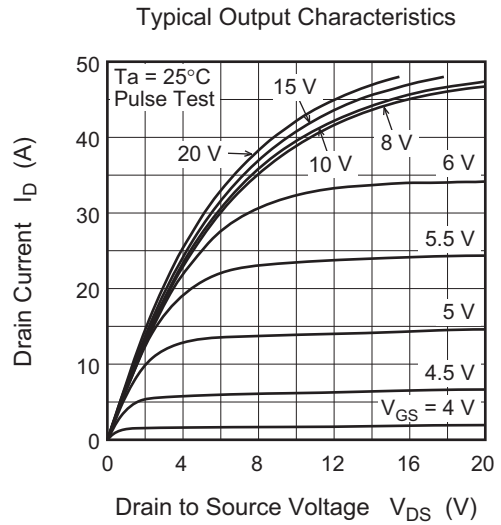
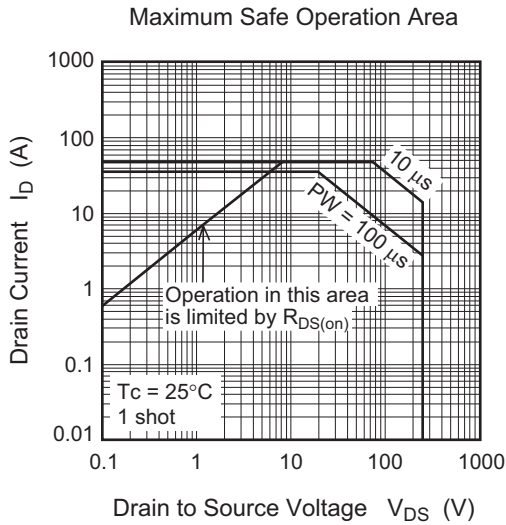
Electrical Characteristics

(Ta = 25°C)

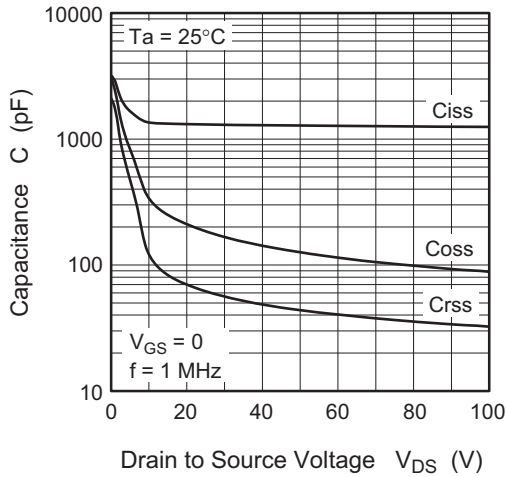
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to Source breakdown voltage	$V_{(BR)DSS}$	250	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Zero Gate voltage drain current	I_{DSS}	—	—	10	μA	$V_{DS} = 250 \text{ V}$, $V_{GS} = 0$
Gate to Source leak current	I_{GSS}	—	—	± 0.1	μA	$V_{GS} = \pm 30 \text{ V}$, $V_{DS} = 0$
Gate to Source cutoff voltage	$V_{GS(off)}$	1.5	—	4.0	V	$V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$
Static Drain to Source on state resistance	$R_{DS(on)}$	—	0.13	0.17	Ω	$I_D = 6 \text{ A}$, $V_{GS} = 10 \text{ V}$
Input capacitance	C_{iss}	—	1300	—	pF	$V_{DS} = 25 \text{ V}$
Output capacitance	C_{oss}	—	185	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	62	—	pF	$f = 1 \text{ MHz}$
Turn-on delay time	$t_{d(on)}$	—	24	—	ns	$I_D = 6 \text{ A}$
Rise time	t_r	—	57	—	ns	$V_{GS} = 10 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	190	—	ns	$R_L = 20 \Omega$
Fall time	t_f	—	69	—	ns	$R_g = 10 \Omega$
Body-Drain diode forward voltage	V_{DF}	—	0.89	1.35	V	$I_F = 12 \text{ A}$, $V_{GS} = 0$
Body-Drain diode reverse recovery time	t_{rr}	—	93	—	ns	$I_F = 12 \text{ A}$, $V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Notes: 4. Pulse test

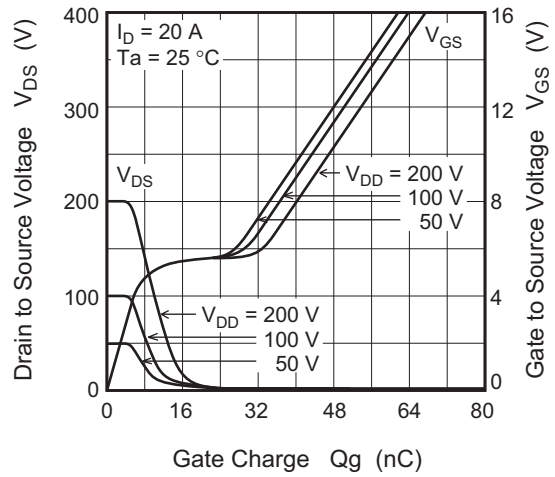
Main Characteristics



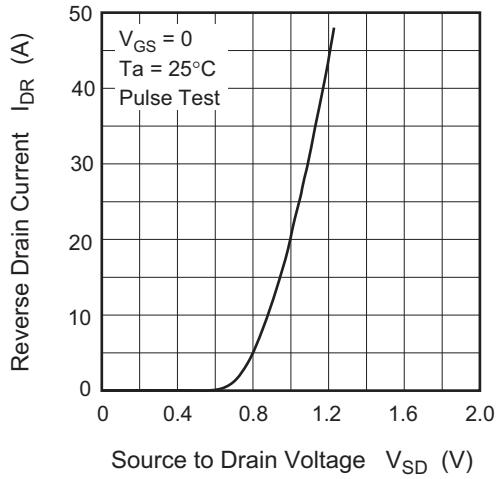
Typical Capacitance vs. Drain to Source Voltage



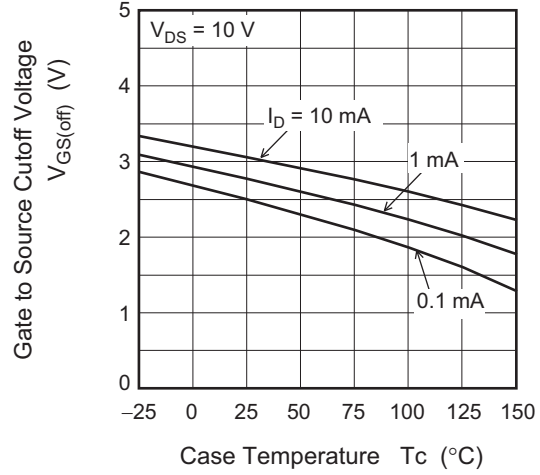
Dynamic Input Characteristics (Typical)



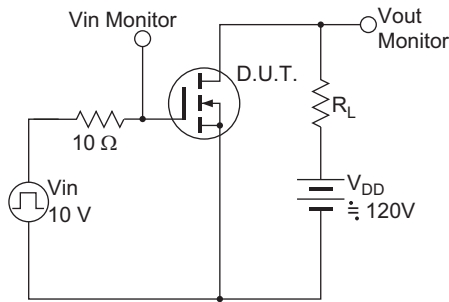
Reverse Drain Current vs. Source to Drain Voltage (Typical)



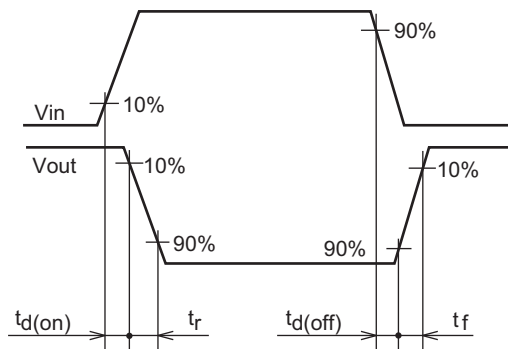
Gate to Source Cutoff Voltage vs. Case Temperature (Typical)



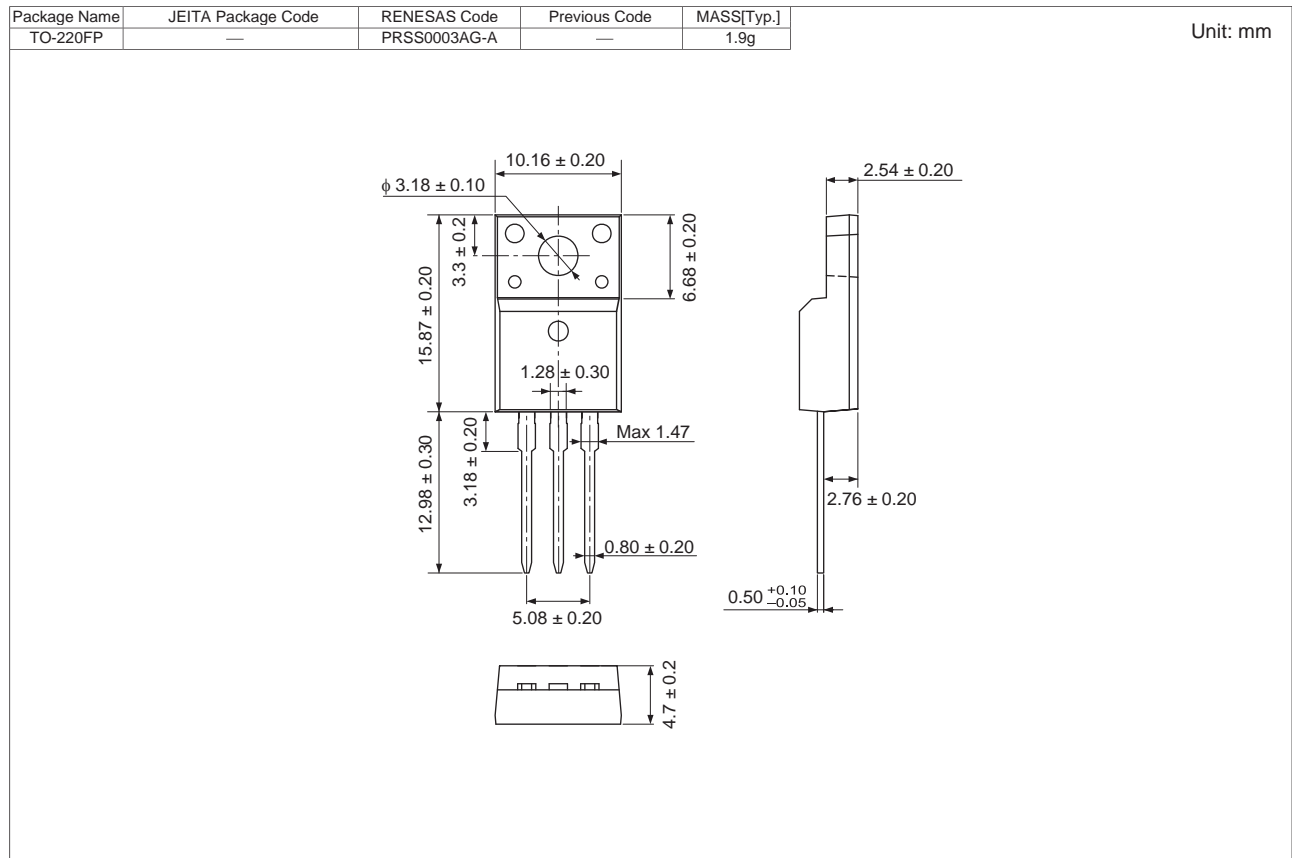
Switching Time Test Circuit



Waveform



Package Dimensions



Ordering Information

Orderable Part Number	Quantity	Shipping Container
H5N2522FP-E0-E#T2	1000 pcs	Box (Tube)

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